### DISCRETE SEMICONDUCTORS

## DATA SHEET

## BT258X series Thyristors logic level

**Product specification** 

October 2002



### Thyristors logic level

BT258X series

#### **GENERAL DESCRIPTION**

# Passivated, sensitive gate thyristors in a full pack, plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

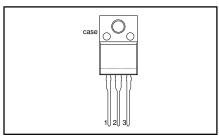
#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT258X- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state	<b>500R</b> 500 5 8 75	600R 600 5 8 75	800R 800 5 8 75	V A A A

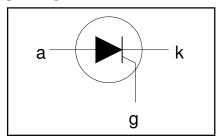
#### **PINNING - SOT186A**

Ī	PIN	DESCRIPTION
	1	cathode
	2	anode
	3	gate
	case	isolated

#### **PIN CONFIGURATION**



#### **SYMBOL**



#### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V <sub>DRM</sub> , V <sub>RRM</sub>	Repetitive peak off-state voltages		-	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	<b>-800R</b> 800	V
I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{hs} \le 90  ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25  ^{\circ}\text{C}$ prior to surge	-	5 8		A A	
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	t = 10  ms t = 8.3  ms t = 10  ms $I_{TM} = 10 \text{ A}; I_G = 50 \text{ mA};$ $dI_G/dt = 50 \text{ mA}/\mu s$	- - -		75 82 28 50		Α Α Α²s Α/μs
I <sub>GM</sub> V <sub>RGM</sub> P <sub>GM</sub> P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	triggering Peak gate current Peak reverse gate voltage Peak gate power Average gate power Storage temperature Operating junction temperature	over any 20 ms period	- - - -40 -	2 5 5 0.5 150 125 <sup>2</sup>		ئي≪>&¢¢	

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

<sup>2</sup> Note: Operation above 110°C may require the use of a gate to cathode resistor of 1kΩ or less.

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#### **ISOLATION LIMITING VALUE & CHARACTERISTIC**

 $T_{hs}$  = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>isol</sub>	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	ı	ı	2500	>
C <sub>isol</sub>	Capacitance from T2 to external heatsink	f = 1 MHz	-	10	-	pF

#### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th j-hs}$ $R_{th j-a}$	Thermal resistance junction to heatsink Thermal resistance junction to ambient	with heatsink compound without heatsink compound in free air		- - 55	5.0 6.9 -	K/W K/W K/W

#### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	50	200	μΑ
I <sub>1</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	0.4	10	mΑ
I <sub>H</sub>	Holding current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$	-	0.3	6	mA
ΙŸ <sub>Τ</sub>	On-state voltage	$I_{T} = 16 \text{ A}$	-	1.3	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.4	1.5	V
]		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 \text{ A}$ ; $T_j = 110 ^{\circ}\text{C}$	0.1	0.2	-	V
$I_{D}, I_{R}$	Off-state leakage current	$V_D = V_{DRM(max)}^{Stationary}; V_R = V_{RRM(max)}; T_j = 125 °C$	-	0.1	0.5	mA

#### **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM}$ = 67% $V_{DRM(max)}$ ; $T_j$ = 125 °C; exponential waveform; $R_{GK}$ = 100 Ω	50	100	-	V/µs
t <sub>gt</sub>	Gate controlled turn-on time	$I_{TM} = 10 \text{ A}; V_D = V_{DRM(max)}; I_G = 5 \text{ mA}; $ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-	2	-	μs
t <sub>q</sub>	Circuit commutated turn-off time	$ \begin{vmatrix} V_{\text{D}} = 67\% \ V_{\text{DRM(max)}}; \ T_{j} = 125 \ ^{\circ}\text{C}; \\ I_{\text{TM}} = 12 \ A; \ V_{\text{R}} = 24 \ V; \ dI_{\text{TM}}/dt = 10 \ A/\mu\text{s}; \\ dV_{\text{D}}/dt = 2 \ V/\mu\text{s}; \ R_{\text{GK}} = 1 \ k\Omega $	-	100	-	μs

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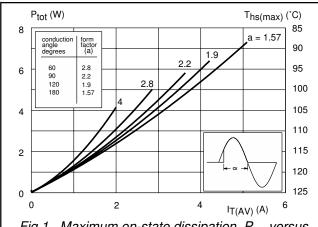


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form \ factor = I_{T(RMS)}/I_{T(AV)}$ .

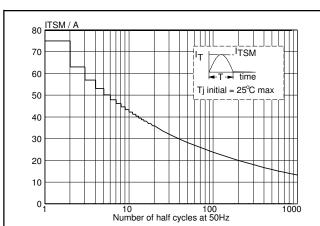


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

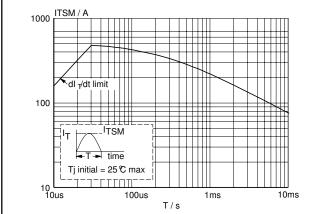


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

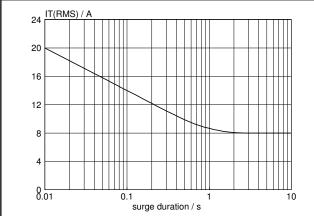


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{hs} \le 90 ^{\circ}\text{C}$ .

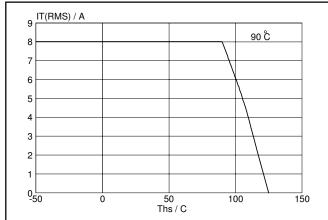
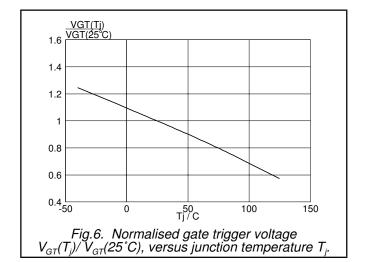


Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{hs}$ .



Rev 2.000

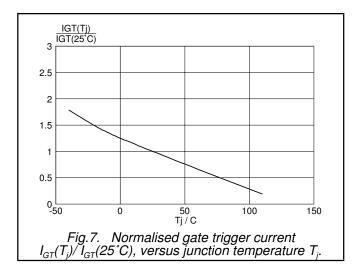
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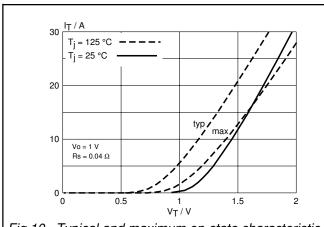
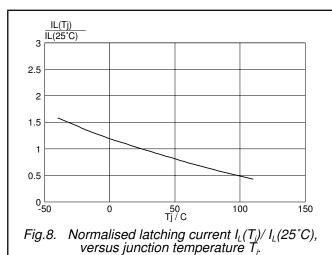


Fig.10. Typical and maximum on-state characteristic.



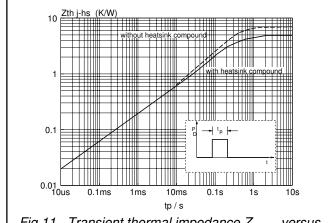


Fig.11. Transient thermal impedance  $Z_{th\,j\text{-}hs}$ , versus pulse width  $t_p$ .

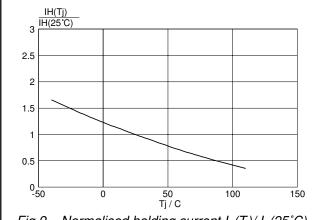


Fig.9. Normalised holding current  $I_H(T_j)/I_H(25^{\circ}C)$ , versus junction temperature  $T_j$ .

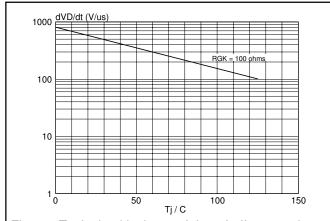


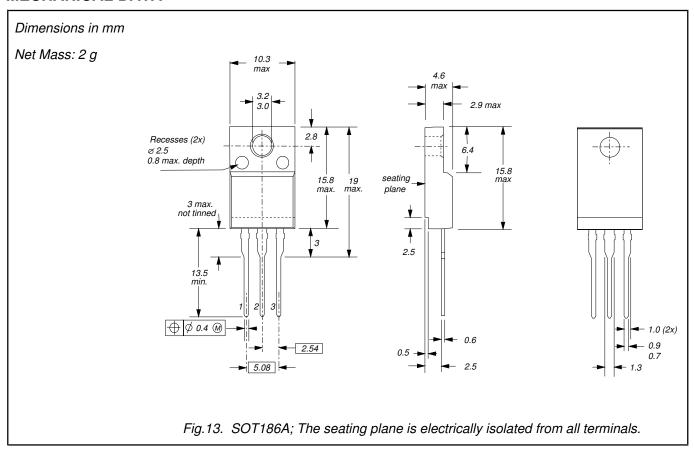
Fig. 12. Typical, critical rate of rise of off-state voltage,  $dV_D/dt$  versus junction temperature  $T_{j\cdot}$ 

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#### **MECHANICAL DATA**



- Notes
  1. Refer to mounting instructions for F-pack envelopes.
  2. Epoxy meets UL94 V0 at 1/8".

#### Legal information

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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